

10/553245

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Form PTO-1449 (REV. 8-83)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. <u>NREL 01-43</u>	SERIAL NO. Not Yet Assigned
INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i> METHOD FOR PRODUCING HIGH CARRIER CONCENTRATION P-TYPE TRANSPARENT CONDUCTING OXIDES		APPLICANT Li et al.	EXAMINER Not Yet Assigned
		FILING DATE	GROUP Not Yet Assigned

U. S. PATENT DOCUMENTS

Examiner INITIAL	REF	DOCUMENT NUMBER	DATE	NAME			FILING DATE IF APPROPRIATE
		4,612,411	09/16/86	Wieting	136	265	
		5,078,803	01/17/92	Pier et al.	136	256	
		5,324,365	06/28/94	Niwa	136	256	
		5,420,043	05/30/95	Niwa	438	96	
		5,458,753	10/17/95	Sato et al.	204	192.29	
		5,578,501	11/26/96	Niwa	438	96	
		5,604,133	02/18/97	Aoike	438	96	
		5,612,229	03/18/97	Yoshida	438	72	
		5,620,924	04/15/97	Takizawa	427	108	

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER _____ DATE CONSIDERED _____

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiner INITIAL	REF	DOCUMENT NUMBER	DATE	NAME			FILING DATE IF APPROPRIATE
		5,716,480	02/10/98	Matsuyama et al.	136	249	
		5,804,466	09/08/98	Arao et al.	438	95	
		5,913,986	06/22/99	Matsuyama	136	255	
		5,990,416	11/23/99	Windisch et al.	136	255	
		6,040,521	03/21/00	Kushiya et al.	136	265	
		6,043,427	03/28/00	Nishimoto	136	258	
		6,107,116	08/22/00	Kariya et al.	438	87	
		6,187,150 B1	02/13/01	Yoshimi et al.	204	192.29	
		6,238,808	05/29/01	Arao et al.	428	629	
		6,424,687B1	06/15/01	Schropp	136	255	

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						YES	NO

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Examiner INITIAL	REF	DOCUMENT NUMBER	DATE	NAME			FILING DATE IF APPROPRIATE
		5,756,207	05/26/1998	Clough et al.			

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							YES	NO

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	AA	M. Joseph et al., "p-type Electrical Conduction in ZnO Thin films by Ga and N Codoping," Jpn. J. Appl. Phys. 38, (1999) pp. L1205-1207
	AB	K. Minegishi et al., "Growth of p-type Zinc oxide Films by Chemical Vapor Deposition," Jpn. J. Appl. Phys. 36, (1997) pp. L1453-L145
	AC	X. Gao et al., "Pulsed Reactive Laser Deposition of p-type ZnO Film Enhanced by an Electron Cyclotron Resonance Source," J. of Crystal Growth, 223 (2001) 135-139
	AD	S. B. Zhang et al. J. Appl. Phys. 83, 3192 (1998).
	AE	Y. Sato et al., Thin Solid Films 281-282, 445 (1996)
	AF	Yan et al. in "Control of Doping by impurity Chemical Potentials: Predictions for p-Type ZnO," Physical Review Letters 86, 5723 (2001)